

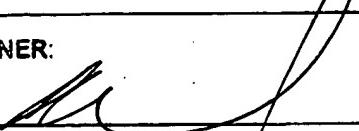
<b>INFORMATION DISCLOSURE STATEMENT</b>		Alty Docket: Serial No.: Applicant: Filing Date: Group:	62603_CON2 NOT YET ASSIGNED MEARS HEREWITH
			

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U.S. PATENT DOCUMENTS							
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
	AA	4,594,603	06/10/86	Holonyak, Jr.	357	16	01/24/85
	AB	4,937,204	06/26/90	Ishibashi et al.	437	110	01/4/89
	AC	4,969,031	11/06/90	Kobayashi et al.	357	63	02/3/83
	AD	5,05,887	10/08/91	Yamazaki	357	4	01/10/90
	AE	5,216,262	06/1/93	Tsu	257	17	03/2/92
	AF	5,357,119	10/18/94	Wang et al.	257	18	02/19/93
	AG	5,684,817	11/04/97	Houdre et al.	372	45	05/17/96
	AH	5,682,934	11/4/03	Candetaria	437	134	05/3/96
	AI	6,004,164	11/30/99	Fonash et al.	438	97	03/18/98
	AJ	6,058,127	05/2/00	Joannepeutes et al.	372	92	12/12/97
	AK	6,274,007	08/14/01	Smirnov et al.	204	192	03/14/00
	AL	6,281,518	08/28/01	Sato	257	13	12/3/98
	AM	6,281,532	08/28/01	Doyle et al.	257	288	06/28/99
	AN	6,344,271	02/05/02	Yadav et al.	428	402	03/23/99
	AO	6,472,685	10/29/02	Takagi	257	77	12/2/98
	AP	6,498,359	12/24/02	Schmidt et al.	257	190	05/18/01
	AQ	2003/0034529	02/20/03	Fitzgerald et al.	257	369	10/8/02
	AR	2003/0057416	03/27/03	Currie et al.	257	19	09/20/02

## FOREIGN PATENT DOCUMENTS

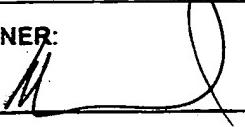
		Document Number	Date	Country	Class	Sub Class	Translation
	AS	02/103767	12/27/02	WO	H01L	21/20	
	AT	2,347,520	09/06/00	GB	G02B	5/18	
	AU						

EXAMINER:	DATE CONSIDERED:
	9/2/05
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;        Draw line through citation if not in conformance and not considered. Include copy of this form with next        communication to applicant.</p>	

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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	AV	Xuan Luo et al.; "Chemical Design of Direct-Gap Light-Emitting Silicon", published July 25, 2002 by The American Physical Society; Vol. 89, Number 7
	AW	R. Tsu, University of North Carolina at Charlotte, "Phenomena in Silicon Nanostructure Devices"; published 09/05/2000 © Springer-Verlag 2000
	AX	P.D. Ye et al. "GaAs MOSFET with Oxide Gate Dielectric Grown by Atomic Layer Deposition", © 2003 Agere Systems, March 2003
	AY	Novikov et al.; "Silicon-based Optoelectronics" © 1999-2003 by John Wiley & Sons, Inc.; pp/ 1-6
	AZ	
	BA	



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**SUBSTITUTE FORM PTO-1449A  
LIST OF PATENTS AND  
APPLICANT'S INFORMATION  
DISCLOSURE STATEMENT**

Atty Docket: 62603\_CON2  
Serial No.: 10/717,370  
Applicant: MEARS ET AL.  
Filing Date: 11/19/03  
Group: 1722

**U.S. PATENT DOCUMENTS**

Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
	AA	4,882,609	11/21/89	Schubert et al.	357	22	
	AB	5,081,513	1/14/92	Jackson et al.	357	23.7	
	AC	5,606,177	2/25/97	Wallace et al.	257	25	
	AD	6,255,150	7/3/01	Wilk et al.	438	191	
	AE	4,908,678	3/13/90	Yamazaki	357	4	
	AF						
	AG						
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	AI						
	AJ						
	AK						
	AL						

**FOREIGN PATENT DOCUMENTS**

		Document Number	Date	Country	Class	Sub Class	Translation
	AM	0 843 361	5/20/98	EP	H01L29	76	
	AN						
	AO						
	AP						

**OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)**

	AQ	Patent Abstracts of Japan, Vol. 012, No. 080 (E-590), 12 March 1988 & JP 62 219665 A (Fujitsu Ltd), 26 September 1987 abstract
	AR	Patent Abstracts of Japan, Vol. 010, No.179 (E-414), 24 June 1986 & JP 61 027681 A (Res Dev Corp of Japan), 7 February 1986 abstract
	AS	

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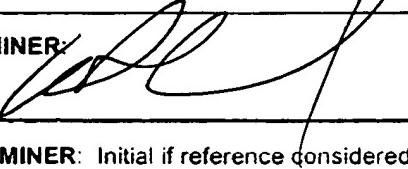
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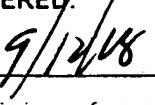
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	AF	5,357,119	10/18/94	Wang et al.	257	18	02/19/93
	AG	5,684,817	11/04/97	Houdre et al.	372	45	05/1/96
	AH	5,683,934	11/4/03	Candelaria	437	134	05/3/96
	AI	5,994,164	11/30/99	Fonash et al.	438	97	03/18/98
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	AK	6,274,007	08/14/01	Smirnov et al.	204	192	03/14/00
	AL	6,281,518	08/28/01	Sato	257	13	12/3/98
	AM	6,281,532	08/28/01	Doyle et al.	257	288	06/28/99
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	AX	P.D. Ye et al., "GaAs MOSFET with Oxide Gate Dielectric Grown by Atomic Layer Deposition"; © 2003 Agere Systems, March 2003
	AY	Novikov et al.; "Silicon-based Optoelectronics" © 1999-2003 by John Wiley & Sons, Inc.; pp/ 1-6
	AZ	
	BA	

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